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Understanding Embedded - Microprocessors

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Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e600
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.5GHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	994-BCBGA, FCCBGA
Supplier Device Package	994-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc8641vu1500kc

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Electrical Characteristics

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8641. The MPC8641 is currently targeted to these specifications.

2.1 **Overall DC Electrical Characteristics**

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Characteristic	Symbol	Absolute Maximum Value	Unit	Notes
Cores supply voltages	V _{DD} _Core0, V _{DD} _Core1	-0.3 to 1.21 V	V	2
Cores PLL supply	AV _{DD} _Core0, AV _{DD} _Core1	–0.3 to 1.21 V	V	_
SerDes Transceiver Supply (Ports 1 and 2)	SV _{DD}	–0.3 to 1.21 V	V	_
SerDes Serial I/O Supply Port 1	XV _{DD} _SRDS1	–0.3 to 1.21V	V	_
SerDes Serial I/O Supply Port 2	XV _{DD} _SRDS2	-0.3 to 1.21 V	V	
SerDes DLL and PLL supply voltage for Port 1 and Port 2	AV _{DD} _SRDS1, AV _{DD} _SRDS2	-0.3 to 1.21V	V	—
Platform Supply voltage	V _{DD} _PLAT	–0.3 to 1.21V	V	
Local Bus and Platform PLL supply voltage	AV _{DD} _LB, AV _{DD} _PLAT	-0.3 to 1.21V	V	—
DDR and DDR2 SDRAM I/O supply voltages	D1_GV _{DD,}	–0.3 to 2.75 V	V	3
	D2_GV _{DD}	–0.3 to 1.98 V	V	3
eTSEC 1 and 2 I/O supply voltage	LV _{DD}	–0.3 to 3.63 V	V	4
		-0.3 to 2.75 V	V	4
eTSEC 3 and 4 I/O supply voltage	TV _{DD}	-0.3 to 3.63 V	V	4
		-0.3 to 2.75 V	V	4
Local Bus, DUART, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I ² C, JTAG and Miscellaneous I/O voltage	OV _{DD}	–0.3 to 3.63 V	V	—



Electrical Characteristics

Characteristic		Symbol	Recommended Value	Unit	Notes
SerDes Serial I/O Supply	Port 1	XV _{DD} _SRDS1	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
SerDes Serial I/O Supply	Port 2	XV _{DD_} SRDS2	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
SerDes DLL and PLL sup	ply voltage for Port 1 and Port 2	AV _{DD} _SRDS1,	1.10 ± 50 mV	V	8
		AV _{DD} _SRDS2	1.05 ± 50 mV		7
Platform Supply voltage		V _{DD} _PLAT	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
Local Bus and Platform Pl	LL supply voltage	AV _{DD} _LB,	1.10 ± 50 mV	V	8
		AV _{DD} _PLAT	1.05 ± 50 mV		7
DDR and DDR2 SDRAM I/O supply voltages		D1_GV _{DD,}	2.5 V ± 125 mV	V	9
		D2_GV _{DD}	1.8 V ± 90 mV	V	9
eTSEC 1 and 2 I/O supply voltage		LV _{DD}	3.3 V ± 165 mV	V	10
			2.5 V ± 125 mV	V	10
eTSEC 3 and 4 I/O supply	/ voltage	TV _{DD}	3.3 V ± 165 mV	V	10
			2.5 V ± 125 mV	V	10
Local Bus, DUART, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I ² C, JTAG and Miscellaneous I/O voltage		OV _{DD}	3.3 V ± 165 mV	V	5
Input voltage	DDR and DDR2 SDRAM signals	D <i>n</i> _MV _{IN}	GND to Dn_GV _{DD}	V	3, 6
	DDR and DDR2 SDRAM reference	Dn_MV _{REF}	$Dn_GV_{DD}/2 \pm 1\%$	V	
	Three-speed Ethernet signals	LV _{IN} TV _{IN}	GND to LV _{DD} GND to TV _{DD}	V	4, 6
	DUART, Local Bus, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I ² C, JTAG and Miscellaneous I/O voltage	OV _{IN}	GND to OV _{DD}	V	5,6

Table 2. Recommended Operating Conditions (continued)

Electrical Characteristics

NOTE

There is no required order sequence between the individual rails for this item (# 1). However, V_{DD} _PLAT, AV_{DD} _PLAT rails must reach 90% of their recommended value before the rail for Dn_GV_DD, and Dn_MV_{REF} (in next step) reaches 10% of their recommended value. AV_{DD} type supplies must be delayed with respect to their source supplies by the RC time constant of the PLL filter circuit described in Section 20.2.1, "PLL Power Supply Filtering."

2. Dn_GV_{DD} , Dn_MV_{REF}

NOTE

It is possible to leave the related power supply $(Dn_GV_{DD}, Dn_MV_{REF})$ turned off at reset for a DDR port that will not be used. Note that these power supplies can only be powered up again at reset for functionality to occur on the DDR port.

3. SYSCLK

The recommended order of power down is as follows:

- 1. Dn_GV_{DD}, Dn_MV_{REF}
- 2. All power rails other than DDR I/O (Dn_GV_{DD} , Dn_MV_{REF}).

NOTE

SYSCLK may be powered down simultaneous to either of item # 1 or # 2 in the power down sequence. Beyond this, the power supplies may power down simultaneously if the preservation of DDRn memory is not a concern.

See Figure 3 for more details on the Power and Reset Sequencing details.



Power Characteristics

3 Power Characteristics

The power dissipation for the dual core MPC8641D device is shown in Table 4.

Power Mode	Core Frequency (MHz)	Platform Frequency (MHz)	V _{DD} _Coren, V _{DD} _PLAT (Volts)	Junction Temperature	Power (Watts)	Notes
Typical				65 °C	32.1	1, 2
Thermal	1500 MHz	600 MHz	1.1 V		43.4	1, 3
Maximum				105 °C	49.9	1, 4
Typical				65 °C	23.9	1, 2
Thermal	1333 MHz	533 MHz	1.05 V		30.0	1, 3
Maximum				105 °C	34.1	1, 4
Typical				65 °C	23.9	1, 2
Thermal	1250 MHz	500 MHz	1.05 V		30.0	1, 3
Maximum				105 °C	34.1	1, 4
Typical				65 °C	23.9	1, 2
Thermal	1000 MHz	400 MHz	1.05 V		30.0	1, 3
Maximum				105 °C	34.1	1, 4
Typical			/	65 °C	16.2	1, 2, 5
Thermal	1000 MHz	500 MHz	0.95 V, 1.05 V		21.8	1, 3, 5
Maximum				105 °C	25.0	1, 4, 5

Table 4. MPC8641D Power Dissipation (Dual Core)

Notes:

1. These values specify the power consumption at nominal voltage and apply to all valid processor bus frequencies and configurations. The values do not include power dissipation for I/O supplies.

- Typical power is an average value measured at the nominal recommended core voltage (V_{DD}_Core*n*) and 65°C junction temperature (see Table 2)while running the Dhrystone 2.1 benchmark and achieving 2.3 Dhrystone MIPs/MHz with one core at 100% efficiency and the second core at 65% efficiency.
- 3. Thermal power is the average power measured at nominal core voltage (V_{DD}_Core*n*) and maximum operating junction temperature (see Table 2) while running the Dhrystone 2.1 benchmark and achieving 2.3 Dhrystone MIPs/MHz on both cores and a typical workload on platform interfaces.
- 4. Maximum power is the maximum power measured at nominal core voltage (V_{DD}_Core*n*) and maximum operating junction temperature (see Table 2) while running a test which includes an entirely L1-cache-resident, contrived sequence of instructions which keep all the execution units maximally busy on both cores.
- 5. These power numbers are for Part Number MC8641Dxx1000NX only. V_{DD} -Coren = 0.95 V and V_{DD} -PLAT = 1.05 V.

DDR and DDR2 SDRAM

Table 15 provides the recommended operating conditions for the DDR SDRAM component(s) when $Dn_GV_{DD}(typ) = 2.5 \text{ V}.$

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
I/O supply voltage	D <i>n_</i> GV _{DD}	2.375	2.625	V	1
I/O reference voltage	Dn_MV _{REF}	$0.49 \times Dn_GV_{DD}$	$0.51 \times Dn_GV_{DD}$	V	2
I/O termination voltage	V _{TT}	D <i>n</i> _MV _{REF} – 0.04	D <i>n</i> _MV _{REF} + 0.04	V	3
Input high voltage	V _{IH}	D <i>n</i> _MV _{REF} + 0.15	D <i>n</i> _GV _{DD} + 0.3	V	—
Input low voltage	V _{IL}	-0.3	D <i>n</i> _MV _{REF} - 0.15	V	—
Output leakage current	I _{OZ}	-50	50	μA	4
Output high current (V _{OUT} = 1.95 V)	I _{ОН}	-16.2	—	mA	—
Output low current (V _{OUT} = 0.35 V)	I _{OL}	16.2	_	mA	—

Table	15 DDR	SDRAM DC	Electrical	Characteristics	for Dn	GV	(tvn)	- 251	/
lable	15. DDn	SURAW DC	Electrical	Characteristics			(LYP)	= 2.5	

Notes:

1. Dn_GV_{DD} is expected to be within 50 mV of the DRAM Dn_GV_{DD} at all times.

2. MV_{REF} is expected to be equal to $0.5 \times Dn_{GV_{DD}}$, and to track $Dn_{GV_{DD}}$ DC variations as measured at the receiver. Peak-to-peak noise on $Dn_{MV_{REF}}$ may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to Dn_MV_{REF}. This rail should track variations in the DC level of Dn_MV_{REF}.

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq D*n*_GV_{DD}.

Table 16 provides the DDR capacitance when $Dn \text{ }_{\text{DD}}(\text{typ})=2.5 \text{ V}$.

Table 16. DDR SDRAM Capacitance for Dn_GV_{DD} (typ) = 2.5 V

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
Input/output capacitance: DQ, DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C _{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $Dn_GV_{DD} = 2.5 V \pm 0.125 V$, f = 1 MHz, $T_A = 25^{\circ}C$, $V_{OUT} = Dn_GVDD/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 17 provides the current draw characteristics for MV_{REF} .

Table 17. Current Draw Characteristics for MV_{REF}

Parameter / Condition	Symbol	Min	Max	Unit	Note
Current draw for MV _{REF}	I _{MVREF}	—	500	μA	1

1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.



Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management

clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back out onto the TSEC n_GTX_CLK pin (while transmit data appears on TSEC $n_TXD[7:0]$, for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSEC n_GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, since the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is relationship between the maximum FIFO speed and the platform speed. For more information see Section 18.4.2, "Platform to FIFO Restrictions."

NOTE

The phase between the output clocks TSEC1_GTX_CLK and TSEC2_GTX_CLK (ports 1 and 2) is no more than 100 ps. The phase between the output clocks TSEC3_GTX_CLK and TSEC4_GTX_CLK (ports 3 and 4) is no more than 100 ps.

A summary of the FIFO AC specifications appears in Table 26 and Table 27.

Table 26. FIFO Mode Transmit AC Timing Specification

At recommended operating conditions with L/TV_{DD} of 3.3 V \pm 5% and 2.5 V \pm 5%.

Parameter/Condition	Symbol	Min	Тур	Max	Unit
TX_CLK, GTX_CLK clock period (GMII mode)	t _{FIT}	7.0	8.0	100	ns
TX_CLK, GTX_CLK clock period (Encoded mode)	t _{FIT}	5.3	8.0	100	ns
TX_CLK, GTX_CLK duty cycle	t _{FITH/} t _{FIT}	45	50	55	%
TX_CLK, GTX_CLK peak-to-peak jitter	t _{FITJ}	—	—	250	ps
Rise time TX_CLK (20%–80%)	t _{FITR}	—	—	0.75	ns
Fall time TX_CLK (80%–20%)	t _{FITF}	—	—	0.75	ns
FIFO data TXD[7:0], TX_ER, TX_EN setup time to GTX_CLK	t _{FITDV}	2.0	—		ns
GTX_CLK to FIFO data TXD[7:0], TX_ER, TX_EN hold time	t _{FITDX}	0.5		3.0	ns

Table 27. FIFO Mode Receive AC Timing Specification

At recommended operating conditions with L/TV_DD of 3.3 V \pm 5% and 2.5 V \pm 5%.

Parameter/Condition	Symbol	Min	Тур	Мах	Unit
RX_CLK clock period (GMII mode)	t _{FIR} 1	7.0	8.0	100	ns
RX_CLK clock period (Encoded mode)	t _{FIR} ¹	5.3	8.0	100	ns
RX_CLK duty cycle	t _{FIRH} /t _{FIR}	45	50	55	%
RX_CLK peak-to-peak jitter	t _{FIRJ}	—	—	250	ps
Rise time RX_CLK (20%-80%)	t _{FIRR}	—	—	0.75	ns
Fall time RX_CLK (80%–20%)	t _{FIRF}	—	—	0.75	ns
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t _{FIRDV}	1.5	—	_	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t _{FIRDX}	0.5	—	_	ns

±100 ppm tolerance on RX_CLK frequency

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Table 29. GMII Receive AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 3.3 V \pm 5% and 2.5 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
RX_CLK clock fall time (80%-20%)	t _{GRXF} 2		_	1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}

2. Guaranteed by design.

3. ±100 ppm tolerance on RX_CLK frequency

Figure 11 provides the AC test load for eTSEC.



Figure 11. eTSEC AC Test Load

Figure 12 shows the GMII receive AC timing diagram.



Figure 12. GMII Receive AC Timing Diagram



8.2.7 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.7.1 RMII Transmit AC Timing Specifications

The RMII transmit AC timing specifications are in Table 36.

Table 36. RMII Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
REF_CLK clock period	t _{RMT}	—	20.0	—	ns
REF_CLK duty cycle	t _{RMTH} /t _{RMT}	35	50	65	%
REF_CLK peak-to-peak jitter	t _{RMTJ}	—	_	250	ps
Rise time REF_CLK (20%-80%)	t _{RMTR}	1.0	_	2.0	ns
Fall time REF_CLK (80%–20%)	t _{RMTF}	1.0	_	2.0	ns
REF_CLK to RMII data TXD[1:0], TX_EN delay	t _{RMTDX}	1.0	_	10.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}

Figure 20 shows the RMII transmit AC timing diagram.



Figure 20. RMII Transmit AC Timing Diagram



10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8641.

10.1 Local Bus DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the local bus interface operating at $OV_{DD} = 3.3 \text{ V}$ DC.

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current $(V_{IN}^{1} = 0 V \text{ or } V_{IN} = OV_{DD})$	I _{IN}	_	±5	μA
High-level output voltage (OV _{DD} = min, I _{OH} = -2 mA)	V _{OH}	OV _{DD} – 0.2	_	V
Low-level output voltage (OV _{DD} = min, I _{OL} = 2 mA)	V _{OL}	—	0.2	V

Table 40. Local Bus DC Electrical Characteristics (3.3 V DC)

Note:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

10.2 Local Bus AC Electrical Specifications

Table 41 describes the timing parameters of the local bus interface at $OV_{DD} = 3.3$ V with PLL enabled. For information about the frequency range of local bus see Section 18.1, "Clock Ranges."

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t _{LBK}	7.5	—	ns	2
Local Bus Duty Cycle	t _{LBKH} /t _{LBK}	45	55	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	t _{LBKSKEW}	—	150	ps	7, 8
Input setup to local bus clock (except LGTA/LUPWAIT)	t _{LBIVKH1}	1.8	—	ns	3, 4
LGTA/LUPWAIT input setup to local bus clock	t _{LBIVKH2}	1.7	—	ns	3, 4
Input hold from local bus clock (except LGTA/LUPWAIT)	t _{LBIXKH1}	1.0	—	ns	3, 4
LGTA/LUPWAIT input hold from local bus clock	t _{LBIXKH2}	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t _{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	t _{LBKHOV1}	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	t _{LBKHOV2}	—	2.2	ns	—
Local bus clock to address valid for LAD	t _{LBKHOV3}		2.3	ns	_

Table 41. Local Bus Timing Parameters (OV_{DD} = 3.3 V)m - PLL Enabled



JTAG

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the MPC8641/D.

11.1 JTAG DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the JTAG interface.

Table 43. JTAG DC Electrical Characteristics

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	- 0.3	0.8	V
Input current $(V_{IN}^{1} = 0 V \text{ or } V_{IN} = V_{DD})$	I _{IN}	—	±5	μA
High-level output voltage (OV _{DD} = min, I _{OH} = −100 μA)	V _{OH}	OV _{DD} - 0.2	_	V
Low-level output voltage (OV _{DD} = min, I _{OL} = 100 μA)	V _{OL}		0.2	V

Note:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

11.2 JTAG AC Electrical Specifications

Table 44 provides the JTAG AC timing specifications as defined in Figure 33 through Figure 35.

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)¹

At recommended operating conditions (see Table 3).

Parameter	Symbol ²	Min	Мах	Unit	Notes
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t _{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t _{JTKHKL}	15	—	ns	_
JTAG external clock rise and fall times	t _{JTGR} & t _{JTGF}	0	2	ns	6
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} t _{JTIVKH}	4 0		ns	4
Input hold times: Boundary-scan data TMS, TDI	t _{JTDXKH} t _{JTIXKH}	20 25		ns	4
Valid times: Boundary-scan data TDO	t _{jtkldv} t _{jtklov}	4 4	20 25	ns	5

l²C

Table 46. I²C AC Electrical Specifications (continued)

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 45).

Parameter	Symbol ¹	Min	Мах	Unit
Noise margin at the HIGH level for each connected device (including hysteresis)	V _{NH}	$0.2 \times OV_{DD}$	_	V

Note:

- 1. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{12DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{12C} clock reference (K) going to the high (H) state or setup time. Also, t_{12SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{12C} clock reference (K) going to the low (L) state or hold time. Also, t_{12PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{12C} clock reference (K) going to the stop condition (P) reaching the valid state (V) relative to the t_{12C} clock reference (K) going to the latter convention is used with the appropriate letter: R (rise) or F (fall).}
- 2. As a transmitter, the MPC8641 provides a delay time of at least 300 ns for the SDA signal (referred to the Vihmin of the SCL signal) to bridge the undefined region of the falling edge of SCL to avoid unintended generation of Start or Stop condition. When MPC8641 acts as the I²C bus master while transmitting, MPC8641 drives both SCL and SDA. As long as the load on SCL and SDA are balanced, MPC8641 would not cause unintended generation of Start or Stop condition. Therefore, the 300 ns SDA output delay time is not a concern. If, under some rare condition, the 300 ns SDA output delay time is required for MPC8641 as transmitter, the following setting is recommended for the FDR bit field of the I2CFDR register to ensure both the desired I²C SCL clock frequency and SDA output delay time are achieved, assuming that the desired I²C SCL clock frequency is 400 KHz and the Digital Filter Sampling Rate Register (I2CDFSRR) is programmed with its default setting of 0x10 (decimal 16):

I ² C Source Clock Frequency	333 MHz	266 MHz	200 MHz	133 MHz
FDR Bit Setting	0x2A	0x05	0x26	0x00
Actual FDR Divider Selected	896	704	512	384
Actual I ² C SCL Frequency Generated	371 KHz	378 KHz	390 KHz	346 KHz

For the detail of I²C frequency calculation, refer to the application note AN2919 "Determining the I²C Frequency Divider Ratio for SCL". Note that the I²C Source Clock Frequency is half of the MPX clock frequency for MPC8641.

- 3. The maximum t_{I2DXKL} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
- 4. Guaranteed by design.
- 5. C_B = capacitance of one bus line in pF.

Figure 32 provides the AC test load for the I^2C .



Figure 36. I²C AC Test Load



High-Speed Serial Interfaces (HSSI)

- The input amplitude requirement
 - This requirement is described in detail in the following sections.



Figure 39. Receiver of SerDes Reference Clocks

13.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the MPC8641D SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below.

- Differential Mode
 - The input amplitude of the differential clock must be between 400 mV and 1600 mV differential peak-peak (or between 200 mV and 800 mV differential peak). In other words, each signal wire of the differential pair must have a single-ended swing less than 800mV and greater than 200 mV. This requirement is the same for both external DC-coupled or AC-coupled connection.
 - For external DC-coupled connection, as described in Section 13.2.1, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 mV and 400 mV. Figure 40 shows the SerDes reference clock input requirement for DC-coupled connection scheme.
 - For external AC-coupled connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to SGND. Each signal wire of the differential inputs is allowed to swing below and above the command mode voltage (SGND). Figure 41 shows the SerDes reference clock input requirement for AC-coupled connection scheme.
- Single-ended Mode
 - The reference clock can also be single-ended. The SDn_REF_CLK input amplitude (single-ended swing) must be between 400 mV and 800 mV peak-peak (from Vmin to Vmax) with SDn_REF_CLK either left unconnected or tied to ground.



Figure 46 shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with MPC8641D SerDes reference clock input's DC requirement.



Figure 46. Single-Ended Connection (Reference Only)



PCI Express

Table 49. Differential Transmitter	· (TX) Output S	Specifications	(continued)
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Symbol	Parameter	Min	Nom	Мах	Units	Comments
T _{TX-IDLE-SET-TO-IDLE}	Maximum time to transition to a valid Electrical idle after sending an Electrical Idle ordered set		_	20	UI	After sending an Electrical Idle ordered set, the Transmitter must meet all Electrical Idle Specifications within this time. This is considered a debounce time for the Transmitter to meet Electrical Idle after transitioning from L0.
T _{TX-IDLE-TO-DIFF-DATA}	Maximum time to transition to valid TX specifications after leaving an Electrical idle condition			20	UI	Maximum time to meet all TX specifications when transitioning from Electrical Idle to sending differential data. This is considered a debounce time for the TX to meet all TX specifications after leaving Electrical Idle
RL _{TX-DIFF}	Differential Return Loss	12	—	—	dB	Measured over 50 MHz to 1.25 GHz. See Note 4
RL _{TX-CM}	Common Mode Return Loss	6	—	—	dB	Measured over 50 MHz to 1.25 GHz. See Note 4
Z _{TX-DIFF-DC}	DC Differential TX Impedance	80	100	120	Ω	TX DC Differential mode Low Impedance
Z _{TX-DC}	Transmitter DC Impedance	40	—	—	Ω	Required TX D+ as well as D- DC Impedance during all states
L _{TX-SKEW}	Lane-to-Lane Output Skew	_	—	500 + 2 UI	ps	Static skew between any two Transmitter Lanes within a single Link
C _{TX}	AC Coupling Capacitor	75	—	—	nF	All Transmitters shall be AC coupled. The AC coupling is required either within the media or within the transmitting component itself. See Note 8.
T _{crosslink}	Crosslink Random Timeout	0			ms	This random timeout helps resolve conflicts in crosslink configuration by eventually resulting in only one Downstream and one Upstream Port. See Note 7.

Notes:

1. No test load is necessarily associated with this value.

- 2. Specified at the measurement point into a timing and voltage compliance test load as shown in Figure 52 and measured over any 250 consecutive TX UIs. (Also refer to the transmitter compliance eye diagram shown in Figure 50)
- 3. A T_{TX-EYE} = 0.70 UI provides for a total sum of deterministic and random jitter budget of T_{TX-JITTER-MAX} = 0.30 UI for the Transmitter collected over any 250 consecutive TX UIs. The T_{TX-EYE-MEDIAN-to-MAX-JITTER} median is less than half of the total TX jitter budget collected over any 250 consecutive TX UIs. It should be noted that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value.
- 4. The Transmitter input impedance shall result in a differential return loss greater than or equal to 12 dB and a common mode return loss greater than or equal to 6 dB over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements is 50 Ω to ground for both the D+ and D- line (that is, as measured by a Vector Network Analyzer with 50 ohm probes—see Figure 52). Note that the series capacitors C_{TX} is optional for the return loss measurement.
- 5. Measured between 20-80% at transmitter package pins into a test load as shown in Figure 52 for both V_{TX-D+} and V_{TX-D-} .
- 6. See Section 4.3.1.8 of the PCI Express Base Specifications Rev 1.0a
- 7. See Section 4.2.6.3 of the PCI Express Base Specifications Rev 1.0a
- 8. MPC8641D SerDes transmitter does not have C_{TX} built-in. An external AC Coupling capacitor is required.



Serial RapidIO



Figure 56. Receiver Input Compliance Mask

Receiver Type	V _{DIFF} min (mV)	V _{DIFF} max (mV)	A (UI)	B (UI)
1.25 GBaud	100	800	0.275	0.400
2.5 GBaud	100	800	0.275	0.400
3.125 GBaud	100	800	0.275	0.400

Table 62. Receiver Input Compliance Mask Parameters Exclusive of Sinusoidal Jitter

15.9 Measurement and Test Requirements

Since the LP-Serial electrical specification are guided by the XAUI electrical interface specified in Clause 47 of IEEE 802.3ae-2002, the measurement and test requirements defined here are similarly guided by Clause 47. In addition, the CJPAT test pattern defined in Annex 48A of IEEE 802.3ae-2002 is specified as the test pattern for use in eye pattern and jitter measurements. Annex 48B of IEEE 802.3ae-2002 is recommended as a reference for additional information on jitter test methods.

15.9.1 Eye Template Measurements

For the purpose of eye template measurements, the effects of a single-pole high pass filter with a 3 dB point at (Baud Frequency)/1667 is applied to the jitter. The data pattern for template measurements is the



Continuous Jitter Test Pattern (CJPAT) defined in Annex 48A of IEEE 802.3ae. All lanes of the LP-Serial link shall be active in both the transmit and receive directions, and opposite ends of the links shall use asynchronous clocks. Four lane implementations shall use CJPAT as defined in Annex 48A. Single lane implementations shall use the CJPAT sequence specified in Annex 48A for transmission on lane 0. The amount of data represented in the eye shall be adequate to ensure that the bit error ratio is less than 10^{-12} . The eye pattern shall be measured with AC coupling and the compliance template centered at 0 Volts differential. The left and right edges of the template shall be aligned with the mean zero crossing points of the measured data eye. The load for this test shall be 100Ω resistive +/- 5% differential to 2.5 GHz.

15.9.2 Jitter Test Measurements

For the purpose of jitter measurement, the effects of a single-pole high pass filter with a 3 dB point at (Baud Frequency)/1667 is applied to the jitter. The data pattern for jitter measurements is the Continuous Jitter Test Pattern (CJPAT) pattern defined in Annex 48A of IEEE 802.3ae. All lanes of the LP-Serial link shall be active in both the transmit and receive directions, and opposite ends of the links shall use asynchronous clocks. Four lane implementations shall use CJPAT as defined in Annex 48A. Single lane implementations shall use the CJPAT sequence specified in Annex 48A for transmission on lane 0. Jitter shall be measured with AC coupling and at 0 Volts differential. Jitter measurement for the transmitter (or for calibration of a jitter tolerance setup) shall be performed with a test procedure resulting in a BER curve such as that described in Annex 48B of IEEE 802.3ae.

15.9.3 Transmit Jitter

Transmit jitter is measured at the driver output when terminated into a load of 100 Ω resistive +/- 5% differential to 2.5 GHz.

15.9.4 Jitter Tolerance

Jitter tolerance is measured at the receiver using a jitter tolerance test signal. This signal is obtained by first producing the sum of deterministic and random jitter defined in Section 8.6 and then adjusting the signal amplitude until the data eye contacts the 6 points of the minimum eye opening of the receive template shown in Figure 8-4 and Table 8-11. Note that for this to occur, the test signal must have vertical waveform symmetry about the average value and have horizontal symmetry (including jitter) about the mean zero crossing. Eye template measurement requirements are as defined above. Random jitter is calibrated using a high pass filter with a low frequency corner at 20 MHz and a 20 dB/decade roll-off below this. The required sinusoidal jitter specified in Section 8.6 is then added to the signal and the test load is replaced by the receiver being tested.



8. Note that for MPC8641 (single core) the solder balls for the following signals/pins are not populated in the package: VDD_Core1 (R16, R18, R20, T17, T19, T21, T23, U16, U18, U22, V17, V19, V21, V23, W16, W18, W20, W22, Y17, Y19, Y21, Y23, AA16, AA18, AA20, AA22, AB23, AC24) and SENSEVDD_Core1 (U20).





NOTES for Figure 58

- 1. All dimensions are in millimeters.
- 2. Dimensions and tolerances per ASME Y14.5M-1994.
- 3. Maximum solder ball diameter measured parallel to datum A.
- 4. Datum A, the seating plane, is defined by the spherical crowns of the solder balls.
- 5. Capacitors may not be present on all devices.
- 6. Caution must be taken not to short capacitors or expose metal capacitor pads on package top.
- 7. All dimensions symmetrical about centerlines unless otherwise specified.
- Note that for MPC8641 (single core) the solder balls for the following signals/pins are not populated in the package: VDD_Core1 (R16, R18, R20, T17, T19, T21, T23, U16, U18, U22, V17, V19, V21, V23, W16, W18, W20, W22, Y17, Y19, Y21, Y23, AA16, AA18, AA20, AA22, AB23, AC24) and SENSEVDD_Core1 (U20).



Name ¹	Package Pin Number	Pin Type	Power Supply	Notes				
IRQ[9]/DMA_DREQ[3]	B30	I	OV _{DD}	10				
IRQ[10]/DMA_DACK[3]	C30	I	OV _{DD}	9, 10				
IRQ[11]/DMA_DDONE[3]	D30	I	OV _{DD}	9, 10				
IRQ_OUT	J26	0	OV _{DD}	7, 11				
	DUART Signals ⁵		- I I					
UART_SIN[0:1]	B32, C32	I	OV _{DD}	_				
UART_SOUT[0:1]	D31, A32	0	OV _{DD}	_				
UART_CTS[0:1]	A31, B31	I	OV _{DD}	—				
UART_RTS[0:1]	C31, E30	0	OV _{DD}	_				
	I ² C Signals							
IIC1_SDA	A16	I/O	OV _{DD}	7, 11				
IIC1_SCL	B17	I/O	OV _{DD}	7, 11				
IIC2_SDA	A21	I/O	OV _{DD}	7, 11				
IIC2_SCL	B21	I/O	OV _{DD}	7, 11				
System Control Signals ⁵								
HRESET	B18	Ι	OV _{DD}	—				
HRESET_REQ	K18	0	OV _{DD}					
SMI_0	L15	Ι	OV _{DD}					
SMI_1	L16	Ι	OV _{DD}	12, <i>S4</i>				
SRESET_0	C20	-	OV _{DD}	—				
SRESET_1	C21	I	OV _{DD}	12, <i>S4</i>				
CKSTP_IN	L18	I	OV _{DD}	—				
CKSTP_OUT	L17	0	OV _{DD}	7, 11				
READY/TRIG_OUT	J13	0	OV _{DD}	10, 25				
	Debug Signals ⁵							
TRIG_IN	J14	I	OV _{DD}	—				
TRIG_OUT/READY	J13	0	OV _{DD}	10, 25				
D1_MSRCID[0:1]/ LB_SRCID[0:1]	F15, K15	0	OV _{DD}	6, 10				
D1_MSRCID[2]/ LB_SRCID[2]	K14	0	OV _{DD}	10, 25				
D1_MSRCID[3:4]/ LB_SRCID[3:4]	H15, G15	0	OV _{DD}	10				
D2_MSRCID[0:4]	E16, C17, F16, H16, K16	0	OV _{DD}	_				

Table 63. MPC8641 Signal Reference by Functional Block (continued)



Table 65. Memory Bus Clocking Specifications

Characteristic	Maximum Pro Frequ	ocessor Core Jency	Unit	Notes	
	1000, 1250, 1	333, 1500MHz	Onit	notes	
	Min	Мах			
Memory bus clock frequency	200	300	MHz	1, 2	

Notes:

1. Caution: The MPX clock to SYSCLK ratio and e600 core to MPX clock ratio settings must be chosen such that the resulting SYSCLK frequency, e600 (core) frequency, and MPX clock frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 18.2, "MPX to SYSCLK PLL Ratio," and Section 18.3, "e600 to MPX clock PLL Ratio," for ratio settings.

2. The memory bus clock speed is half the DDR/DDR2 data rate, hence, half the MPX clock frequency.

Table 66.	Platform/MPX	bus Clocking	Specifications	

	Maximum Processor Core Frequency		Unit	Notes
Characteristic	1000, 1250, 1333, 1500MHz			
	Min	Мах		
Platform/MPX bus clock frequency	400	500-600	MHz	1, 2

Notes:

1. **Caution:** The MPX clock to SYSCLK ratio and e600 core to MPX clock ratio settings must be chosen such that the resulting SYSCLK frequency, e600 (core) frequency, and MPX clock frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 18.2, "MPX to SYSCLK PLL Ratio," and Section 18.3, "e600 to MPX clock PLL Ratio," for ratio settings.

2. Platform/MPX frequencies between 400 and 500 MHz are not supported.

Table 67. Local Bus Clocking Specifications

	Maximum Processor Core Frequency		Unit	Notes
Characteristic	1000, 1250, 1333, 1500MHz			
	Min	Мах		
Local bus clock speed (for Local Bus Controller)	25	133	MHz	1

Notes:

1. The Local bus clock speed on LCLK[0:2] is determined by MPX clock divided by the Local Bus PLL ratio programmed in LCRR[CLKDIV]. See the reference manual for the MPC8641D for more information on this.

18.2 MPX to SYSCLK PLL Ratio

The MPX clock is the clock that drives the MPX bus, and is also called the platform clock. The frequency of the MPX is set using the following reset signals, as shown in Table 68:

• SYSCLK input signal



Another useful equation is:

$$\mathbf{V}_{H} - \mathbf{V}_{L} = \mathbf{n} \frac{\mathbf{KT}}{\mathbf{q}} \left[\mathbf{In} \frac{\mathbf{I}_{H}}{\mathbf{I}_{L}} \right]$$

Where:

 $I_{fw} = Forward current$ $I_s = Saturation current$ $V_d = Voltage at diode$ $V_f = Voltage forward biased$ $V_H = Diode voltage while I_H is flowing$ $V_L = Diode voltage while I_L is flowing$ $I_H = Larger diode bias current$ $I_L = Smaller diode bias current$ $q = Charge of electron (1.6 \times 10^{-19} \text{ C})$ n = Ideality factor (normally 1.0) $K = Boltzman's constant (1.38 \times 10^{-23} \text{ Joules/K})$ T = Temperature (Kelvins)

The ratio of I_H to I_L is usually selected to be 10:1. The above simplifies to the following:

$$V_{H}-V_{L}=~1.986\times10^{-4}\times nT$$

Solving for T, the equation becomes:

$$\mathbf{nT} = \frac{\mathbf{V}_{\mathsf{H}} - \mathbf{V}_{\mathsf{L}}}{1.986 \times 10^{-4}}$$